

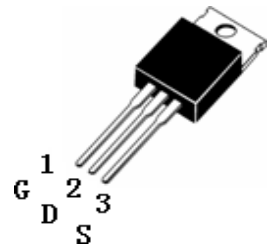
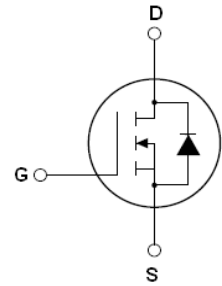
Features:

- Advanced trench process technology
- Special designed for Convertors and power controls
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current
- Avalanche Energy 100% test

ID=80A

BV=80V

Rdson=6.5m Ω (Typ.)



Description:

The SSF7509 is a new generation of middle voltage and high current N-Channel enhancement mode trench power MOSFET. This new technology increases the cell density and reduces the on-resistance; its typical Rdson can reduce to 6.5mohm.

Application:

- Power switching application

SSF7509 TOP View (TO220)

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D@T_c=25\text{ }^{\circ}\text{C}$	Continuous drain current, VGS@10V	80	A
$I_D@T_c=100^{\circ}\text{C}$	Continuous drain current, VGS@10V	72	
I_{DM}	Pulsed drain current ①	320	
$P_D@T_c=25^{\circ}\text{C}$	Power dissipation	165	W
	Linear derating factor	2.0	W/ C
V_{GS}	Gate-to-Source voltage	±20	V
dv/dt	Peak diode recovery voltage	31	v/ns
E_{AS}	Single pulse avalanche energy ②	500	mJ
E_{AR}	Repetitive avalanche energy	TBD	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

Thermal Resistance

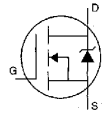
	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case	—	0.75	—	°C/W
$R_{\theta JA}$	Junction-to-ambient	—	—	62	

Electrical Characteristics @TJ=25 °C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source breakdown voltage	80	—	—	V	$V_{GS}=0V, I_D=250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	0.0065	0.008	Ω	$V_{GS}=10V, I_D=40A$
$V_{GS(th)}$	Gate threshold voltage	2.0	3.0	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
g_{fs}	Forward transconductance	—	67	—	S	$V_{DS}=5V, I_D=30A$
I_{DSS}	Drain-to-Source leakage current	—	—	2	μA	$V_{DS}=80V, V_{GS}=0V$
		—	—	10		$V_{DS}=80V, V_{GS}=0V, T_J=150^{\circ}\text{C}$

I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS}=20V$
	Gate-to-Source reverse leakage	—	—	-100		$V_{GS}=-20V$
Q_g	Total gate charge	—	93.6	—	nC	$I_D=30A$
Q_{gs}	Gate-to-Source charge	—	20.2	—		$V_{DD}=30V$
Q_{gd}	Gate-to-Drain("Miller") charge	—	33.3	—		$V_{GS}=10V$
$t_{d(on)}$	Turn-on delay time	—	17.3	—	nS	$V_{DD}=30V$
t_r	Rise time	—	15.2	—		$I_D=2A, R_L=15\Omega$
$t_{d(off)}$	Turn-Off delay time	—	52	—		$R_G=2.5\Omega$
t_f	Fall time	—	19	—		$V_{GS}=10V$
C_{iss}	Input capacitance	—	3200	—	pF	$V_{GS}=0V$
C_{oss}	Output capacitance	—	330	—		$V_{DS}=25V$
C_{rss}	Reverse transfer capacitance	—	260	—		$f=1.0MHz$

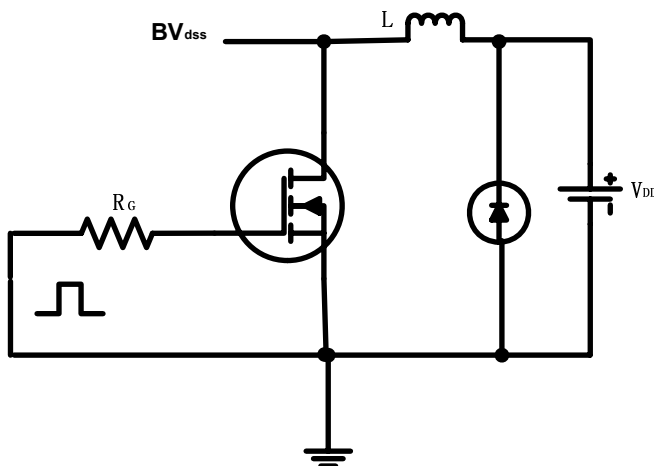
Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _S	Continuous Source Current. (Body Diode)	—	—	80	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	320		
V _{SD}	Diode Forward Voltage	—	—	0.859	V	T _J =25°C, I _S =40A, V _{GS} =0V ③
t _{rr}	Reverse Recovery Time	—	35.9	—	nS	T _J =25°C, I _F =75A di/dt=100A/μs ③
Q _{rr}	Reverse Recovery Charge	—	62.5	—	nC	
t _{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _s + L _D)				

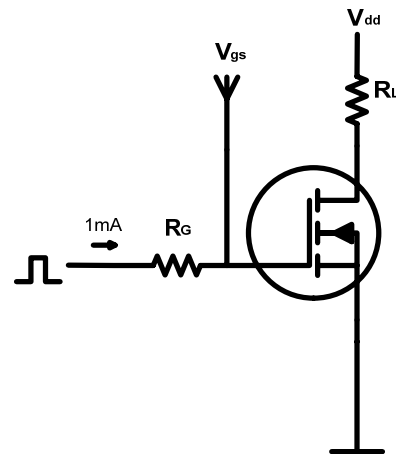
Notes:

- ① Repetitive rating; pulse width limited by max junction temperature.
- ② Test condition: $L = 0.3mH, I_D = 57A, V_{DD} = 47V$
- ③ Pulse width $\leq 300\mu s$; duty cycle $\leq 1.5\%$ $R_G = 25\Omega$ Starting $T_J = 25^\circ C$

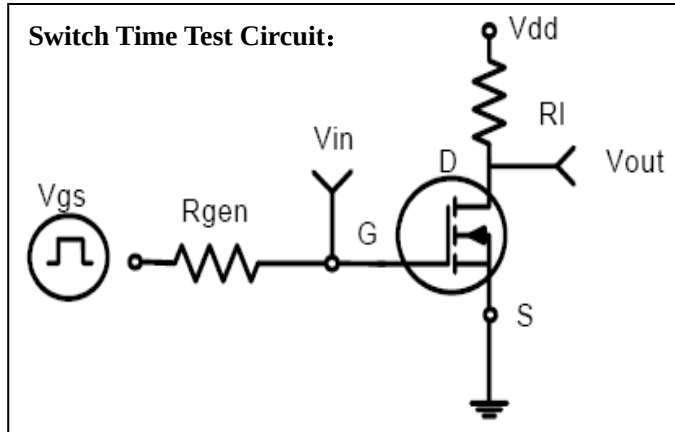
EAS test circuits:



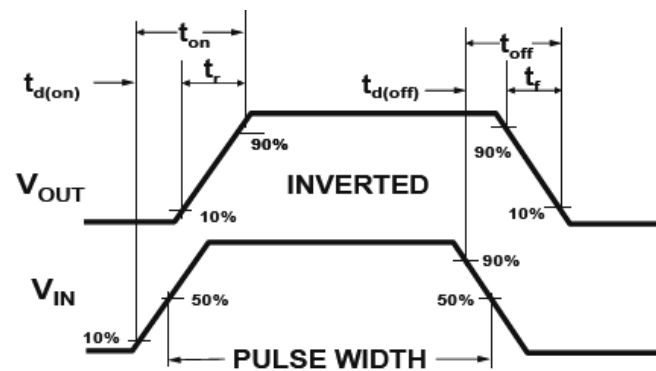
Gate charge test circuit:

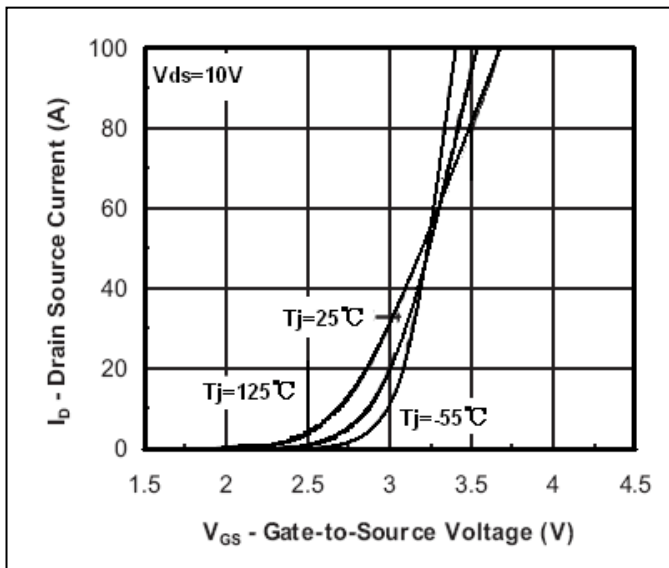


Switch Time Test Circuit:

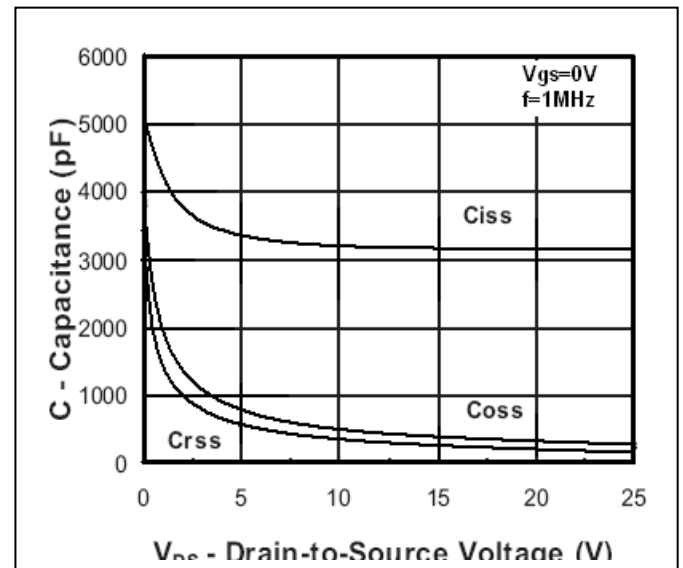


Switch Waveforms:

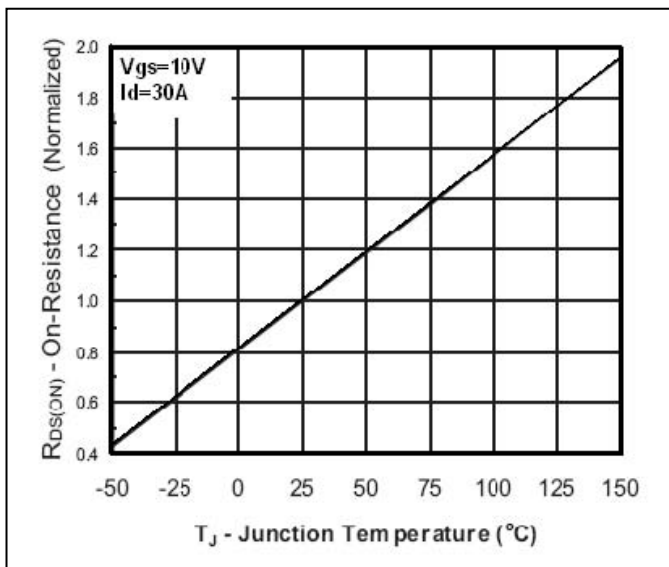




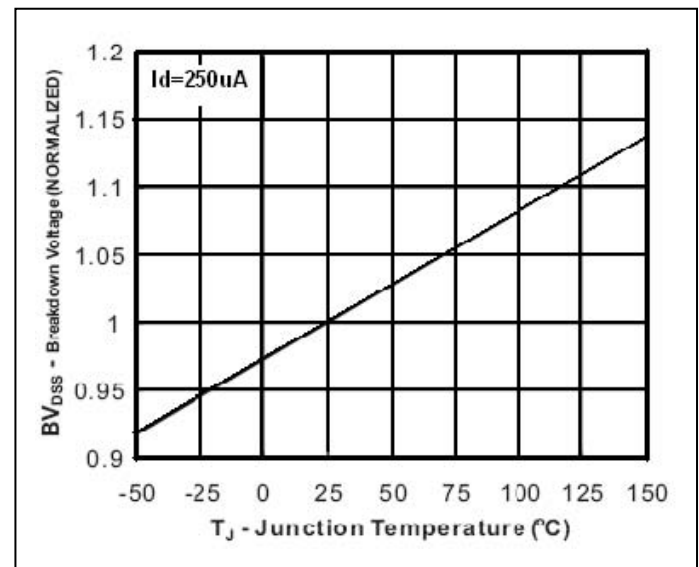
Transfer Characteristic



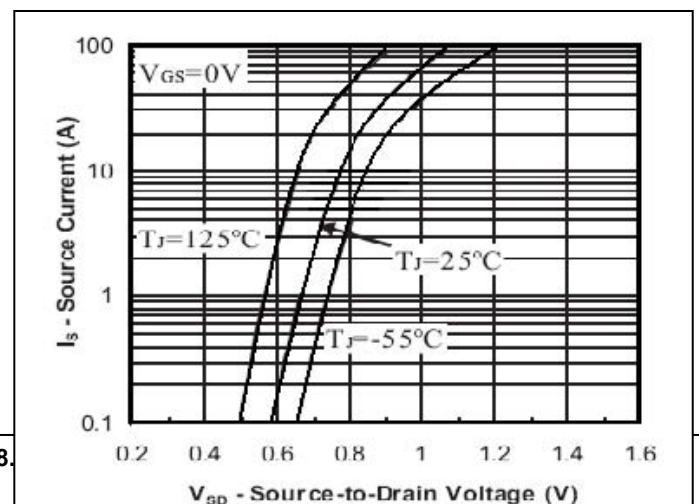
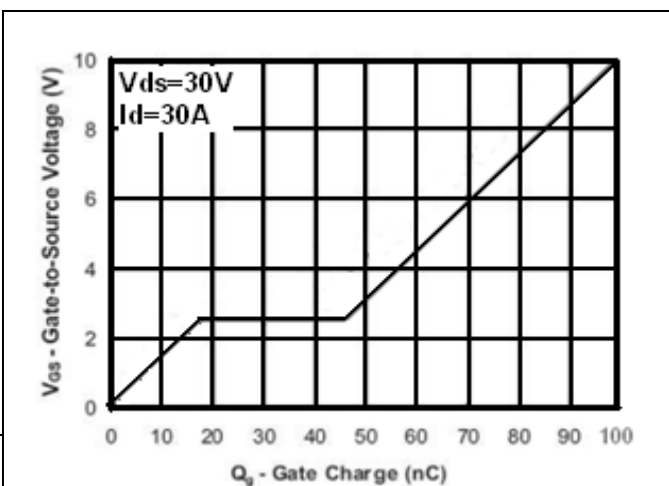
Capacitance



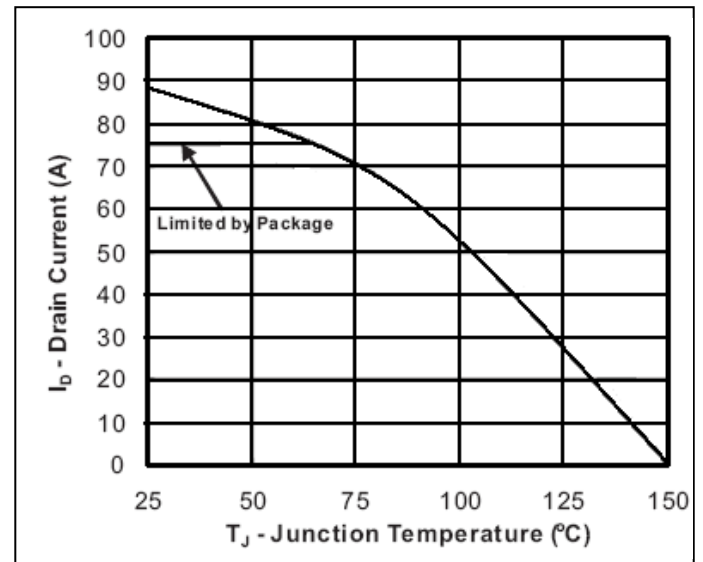
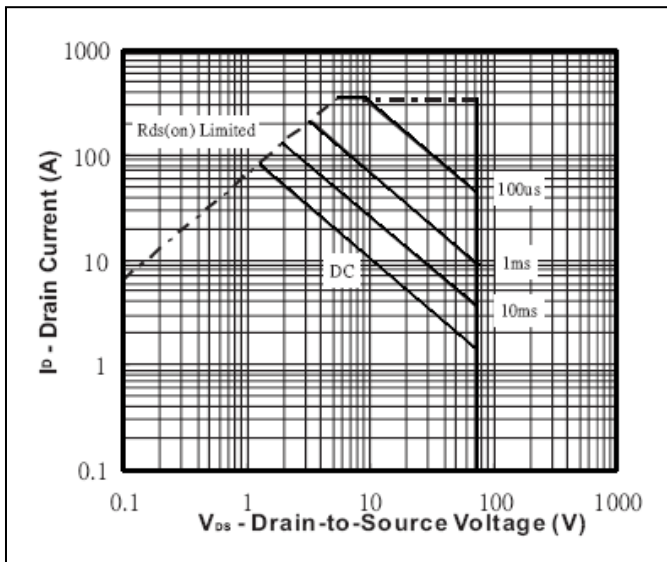
On Resistance vs. Junction Temperature



Breakdown Voltage vs. Junction Temperature

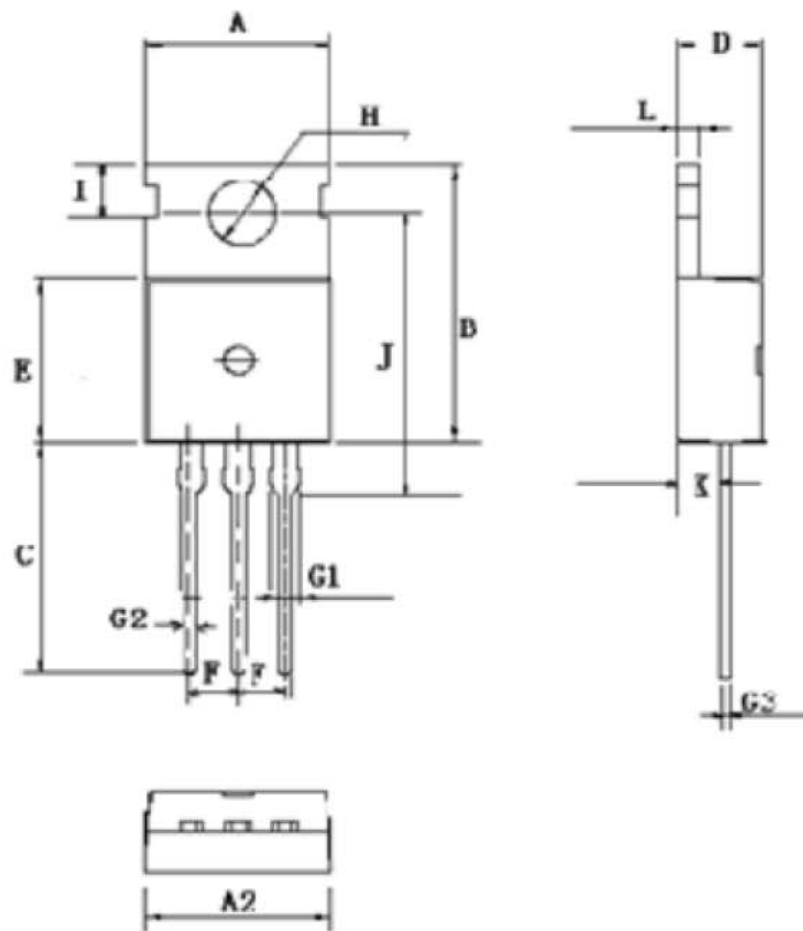


Source-Drain Diode Forward Voltage



Transient Thermal Impedance Curve

TO220 MECHANICAL DATA:



TO-220 3L

图形对应符号	产品外形尺寸
A(mm)	9.66~10.28
A2(mm)	9.80~10.20
B(mm)	15.6~15.8
C(mm)	12.70~14.27
D(mm)	4.30~4.70
E(mm)	8.59~9.40
F(mm)	2.54 (nom)
G1(mm)	1.42~1.62
G2(mm)	0.70~0.95
G3(mm)	0.45~0.60
H(mm) dia.	3.50~3.70
I(mm)	2.7~2.9
J(mm)	15.70~16.25
K(mm)	2.20~2.90
L(mm)	1.15~1.40
M(mm)	0.5